















ESD

TVS

MOS

LDO

Diode

Sensor

DC-DC

Product Specification

Domestic Part Number	SI2301B
Overseas Part Number	SI2301B
▶ Equivalent Part Number	SI2301B





SI2301B P-Channel 20-V(D-S) MOSFET

V _{(BR)DSS}	R _{DS(on)} MAX	I _D
-20 V	120 mΩ@-4.5V	0.7.4
	150 mΩ@-2.5V	2.5 A



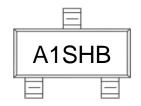
FEATURE

TrenchFET Power MOSFET

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



Maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V _{DS}	-20	V	
Gate-Source Voltage	V_{GS}	±8	V	
Continuous Drain Current (T _J =150℃)	I _D	-2.5		
Pulsed Drain Current	I _{DM}	-10	Α	
Continuous Source-Drain Diode Current	Is	-0.72		
Maximum Power Dissipation	PD	0.35	W	
Thermal Resistance from Junction to Ambient(t≤5s)	R _{θJA}	357	°C/W	
Junction Temperature	TJ	150	0.0	
Storage Temperature	T _{stg}	-55 ~+150	\neg	



T_a=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Тур	Max	Units	
Static			•				
Drain-source breakdown voltage	V(BR)DSS	$V_{(BR)DSS}$ $V_{GS} = 0V$, $I_D = -250\mu A$					
Gate-source threshold voltage	VGS(th)	V _{DS} =V _{GS} , I _D =-250μA	-0.4		-1	V	
Gate-source leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA	
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA	
	1	V _{GS} =-4.5V, I _D =-2.8A		0.095	0.120	Ω	
Drain-source on-state resistance ^a	RDS(on)	V _{GS} =-2.5V, I _D =-2.0A		0.120	0.150		
Forward transconductance ^a	g _{fs}	V _{DS} =-5V, I _D =-2.8A		4.0		S	
Dynamic ^b							
Input capacitance	C _{iss}			405		pF	
Output capacitance	Coss	V _{DS} =-10V,V _{GS} =0V,f =1MHz		75			
Reverse transfer capacitance	C _{rss}			55			
Total gate charge	Qg	V _{DS} =-10V,V _{GS} =-4.5V,I _D =-3A		5.5	10		
Total gate charge				3.3	6	nC	
Gate-source charge	Q _{gs}	V _{DS} =-10V,V _{GS} =-2.5V,I _D =-3A		0.7			
Gate-drain charge	Q_{gd}			1.3			
Gate resistance	R_g	f=1MHz		6.0		Ω	
Turn-on delay time	td(on)	V 40V		11	20		
Rise time	tr	V _{DD} =-10V,		35	60	ns	
Turn-off delay time	td(off)	R_L =10Ω, I_D =-1A, V_{GEN} =-4.5V, R_Q =1Ω		30	50		
Fall time	t f	V _{GEN} 4.5V,Ng-112		10	20		
Drain-source body diode characterist	ics		•	•			
Continuous source-drain diode current	I _S	T _C =25℃			-1.3	А	
Pulse diode forward current ^a	I _{SM}				-10		
Body diode voltage	V _{SD}	I _S =-0.7A		-0.8	-1.2	V	

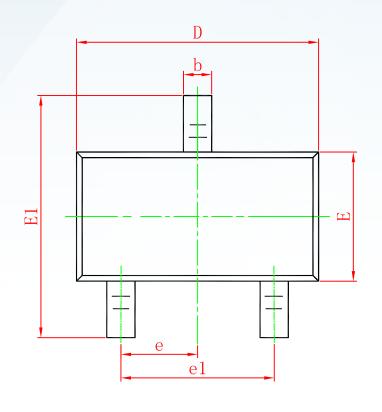
Notes:

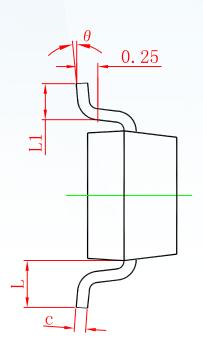
a.Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

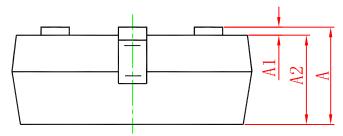
b.Guaranteed by design, not subject to production testing.



SOT-23 PACKAGE OUTLINE DIMENSIONS







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP.	0.037	TYP.	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF.		0.022 REF.		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	



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